

# MULTI-GIGABIT WIRELESS DATA TRANSFER AT 60 GHz

H.K. Soltevit, A. Schöning, R. Brenner and D. Wiedner

Physikalisches Institut University of Heidelberg, Germany, Uppsala University, Department of Physics and Astronomy, Sweden

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## Motivation

- The ATLAS and CMS experiments@LHC consists of several million channels
- Data Transfer rate is today limited by the available:

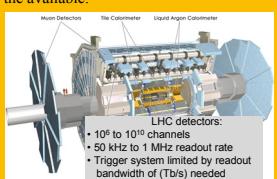
### Bandwidth

limited by

- Power budget (Gbps/W)
- Mass (Gbps/g)
- Space (Gbps/cm<sup>2</sup>)

#### Example: Innermost silicon layer:

- Required bandwidth is 50-100TB/s
- Detector divided into 20-50K independent segments
- Required bandwidth per link is then 5 GB/s



Nordic Neutrino - Electromagnetic - ECAL Trigger - Pixel Detector - MUON trigger

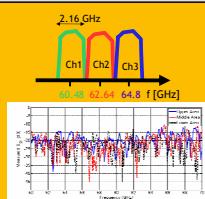
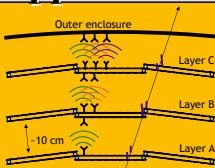
• 10<sup>6</sup> to 10<sup>10</sup> channels  
• 50 kHz to 1 MHz readout rate  
• Trigger system limited by readout bandwidth of (Tb/s) needed

### Use of the Millimeter Wave (MM-Wave) technology at 60 GHz

#### Offers:

- Wireless unlicensed spectrum of 7-9 GHz bandwidth available world-wide.
- Largely unused today: **low interference probability**
- 60 GHz** does not penetrate walls: **security**
- Able to send **Gigabits/s** (depend on modulation sch.) of information over short distance (1-10m) and **LOS** relaxes a few physical limitations
- Small form factor
- High transmit power: **40 dBm EIRP** (Effective Isotropic Radiated Power) allowed in most regions.
- Flexibility of placement and no cables needed
- Allows for integration of antenna(s)

## Our Approach

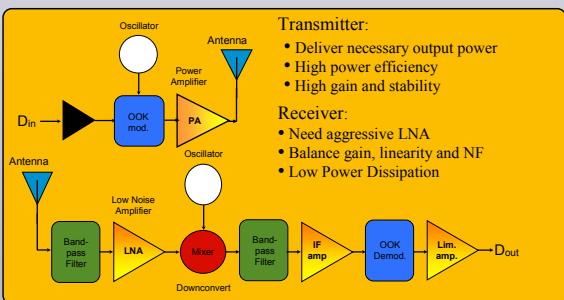


Short distance if readout radially.

• 60 GHz signal cannot penetrate through the silicon layers

- Solution:**
- Send the data through the Silicon layers by a wire connection, with an antenna on both sides.

## Transceiver Architecture



## Link Budget Calculation

Required Bit-Error-Rate (BER: 10<sup>-12</sup>)

OOK Modulation: ( $E_b/N_0 = 17\text{dB}$ )

$$SNR_{min} = \left( \frac{E_b}{N_0} \right) \cdot \frac{R}{B} = 14\text{ dB}$$

$$P_{RX} = SNR_{min} \cdot N_0 \cdot B \cdot F = -57\text{ dBm}$$

• Eb/No: Energy per bit to noise power spectral density

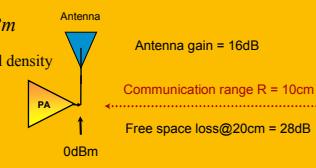
- R: Data bit rate
- B: Bandwidth
- F: Noise Figure
- PRX: Receiver sensitivity

$$P_{TX} = P_{IN} + G_{TX} - L_{TX} - L_M + G_{RX} - L_{RX} = -57\text{ dBm}$$

$$SNR_{in} = P_{in} - N_{Floor}$$

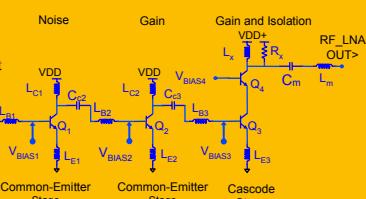
$$N_{Floor} = -174\text{ dBm}/\text{Hz} + 10\log(B) = -77\text{ dBm}$$

$$NF_{RX} = SNR_{in} - SNR_{o(min)} = P_{in} + 174\text{ dBm}/\text{Hz} - 10\log(B) - (E_b/N_0) - (R/B)\text{dB} = 7\text{dB}$$

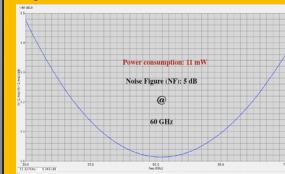


## Low Noise Amplifier (LNA)

- Low Noise Figure NF<sub>min</sub>
- Low Power Consumption
- Large gain to reduce NF<sub>tot</sub>
- Handle large signal without distortion
- Input, output impedance matching
- Isolation between V<sub>s</sub> input and output



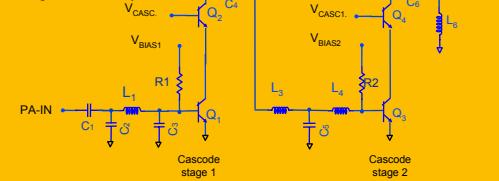
- Sets a lower limit of the entire system
- Optimized for minimum NF and maximum gain



- Noise Figure NF: 5dB
- Reverse Isolation S<sub>12</sub>: -20 dBm
- P<sub>1dB</sub>: -20dBm
- Gain: 20dB
- 3dB bandwidth: 20 GHz
- Power supply: 1.5V
- Power consumption: 11mW
- Input match S<sub>11</sub>: -40 dB
- Input/output imped.: 50 Ω

## Power Amplifier

- Class of operation: AB
- Drive the Antenna
- Trade off of good linearity and good efficiency



- Provide the signal with the required power level to insure that the transmitted signal reaches the receiver with the required power level.
- To provide high gain, and improve the Power Added Efficiency (PAE) and isolation is a two-stage cascode topology chosen.

## Technology

### SiGe HBT BiCMOS compared to CMOS

- For equal performance, SiGe requires less aggressive lit.(2.gen.)
- Higher breakdown voltage at fixed performance
- Much larger gm/um<sup>2</sup> (need big MOSFETs for high fmax)
- Lower 1/f noise
- Modeling is easier for high frequency design
- Matching is superior compared to CMOS devices
- Radiation hardness

**SiGe BiCMOS technology combines both high speed HBTs with relatively high breakdown voltage and standard CMOS transistors allowing a very high integration level**

## 3-D Development

- Better electrical performance
- Lower power consumption and noise
- Smaller wire-length will decrease the average load capacitance and resistance.
- Lower wire to wire capacitance reduce noise coupling between signal lines.
- Form factor improvement
- Lower cost
- More functionality
- Heterogeneous integration



- Move from horizontal 2-D chip layouts to 3-D chip stacking.
- Increased performance - Outscaling Moores's law (More than Moore).
- Decreasing system risk.
- E.g. Stacking a 130 nm analog die with a 65 nm digital die, rather than trying to build a 65 nm mixed signal SOC.
- Reducing cost: at some point, 3-D integration will be cheaper than shrinking further the 2-D design.

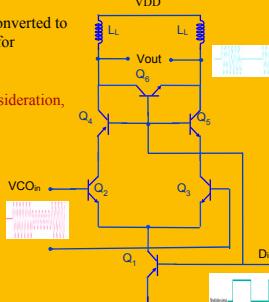
## Preliminary

- Compression point P1dB: 20dBm
- Forward gain S<sub>21</sub>: 30dB
- Reverse Isolation S<sub>12</sub>: -65dB
- Power Added Efficiency: 25dBm

Analog or Digital information is converted to signals at RF frequencies suitable for transmission.

Modulation technique is a key consideration, since it determines:

- System bandwidth
- Efficiency
- Power efficiency
- Sensitivity
- Complexity



## References

- ATLAS Tracking Trigger: Matt Warren ACES 2011
- Radio Frequency Integrated Circuit Design: J. W. M. Rogers and C. Plett
- R.Brenner and S. Cheng, "Multigigabit wireless transfer of trigger data through millimetre wave technology" Workshop on Intelligent Trackers 2010
- H.K. Soltevit et al, "Multi-Gigabit wireless transfer at 60 GHz" Workshop on Intelligent Trackers 2012

## Conclusions

- mm-wave technology presented as a possible solution for current bandwidth limitations of LHC experiments (ATLAS, CMS)
- A 60 GHz transceiver has been proposed
- Schematic of some blocks shown
- Simulations of some blocks shown
- SiGe BiCMOS (and CMOS) technology very well suited for 60 GHz wireless communication front-ends.
- There are several challenges to integration of mm-wave systems on a silicon substrate in spite of its numerous advantages
- 3-D integration opens up new possibilities for the near future that can potentially remove the drawbacks of the 2D solution.

## Voltage Controlled Oscillator

### Used as the Local Oscillator (LO) for the modulation and the mixer

- Accuracy of oscillation
- Phase noise
- Tuning sensitivity and linearity
- Output power

- The voltage controlled frequency of operation is achieved by a voltage dependent capacitance.
- The VCO provides the reference frequency to modulate/demodulate the RF signal.
- Coulpits topology is chosen for low-phase noise and high frequency behavior.

